



STPS20H100CT/CF/CG/CG-1

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

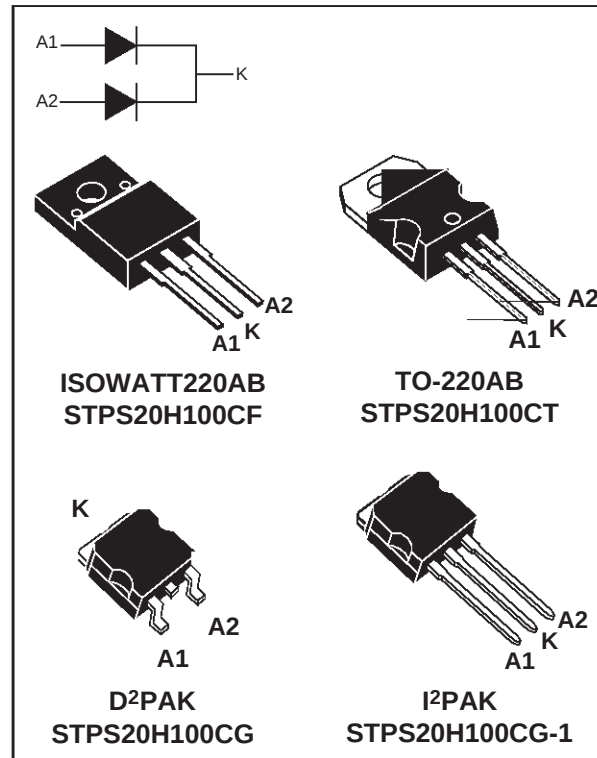
$I_{F(AV)}$	2 x 10 A
V_{RRM}	100 V
T_j	175°C
$V_F (max)$	0.64 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- HIGH JUNCTION TEMPERATURE CAPABILITY
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW LEAKAGE CURRENT
- AVALANCHE RATED
- INSULATED PACKAGE: ISOWATT220AB
Insulating Voltage = 2000V DC
Capacitance = 45 pF

DESCRIPTION

Dual center tap schottky rectifier designed for high frequency miniature Switched Mode Power Supplies such as adaptators and on board DC/DC converters.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V _{RRM}	Repetitive peak reverse voltage				100	V
I _{F(RMS)}	RMS forward current				30	A
I _{F(AV)}	Average forward current δ = 0.5	TO-220AB D ² PAK / I ² PAK	T _c = 160°C	per diode per device	10	A
		ISOWATT220AB	T _c = 145°C		20	
I _{FSM}	Surge non repetitive forward current		tp = 10 ms sinusoidal		250	A
I _{RRM}	Repetitive peak reverse current		tp = 2 μs square F = 1kHz		1	A
I _{RSM}	Non repetitive peak reverse current		tp = 100 μs square		3	A
T _{stg}	Storage temperature range				- 65 to + 175	°C
T _j	Maximum operating junction temperature *				175	°C
dV/dt	Critical rate of rise of reverse voltage				10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / D ² PAK / I ² PAK	Per diode	1.6
		ISOWATT220AB	Per diode	4
		TO-220AB / D ² PAK / I ² PAK	Total	0.9
		ISOWATT220AB	Total	3.2
$R_{th(c)}$		TO-220AB / D ² PAK / I ² PAK	Coupling	0.15
		ISOWATT220AB	Coupling	2.5

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			4.5	μA
		$T_j = 125^\circ\text{C}$			2	6	mA
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$			0.71	V
		$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$			0.77	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$			0.81	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$			0.88	
		$T_j = 125^\circ\text{C}$	$I_F = 8\text{ A}$		0.56	0.58	
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$		0.59	0.64	
		$T_j = 125^\circ\text{C}$	$I_F = 16\text{ A}$		0.65	0.68	
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$		0.67	0.73	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$
 ** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.55 \times I_{F(AV)} + 0.009 \times I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

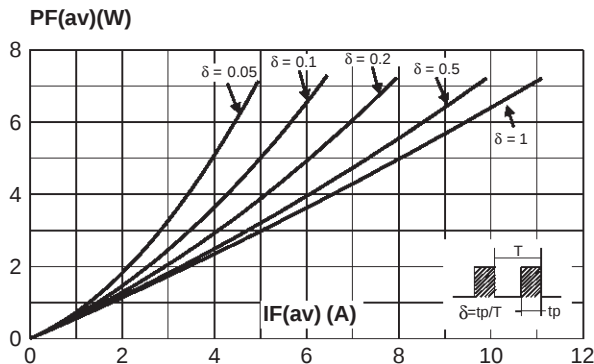


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$, per diode).

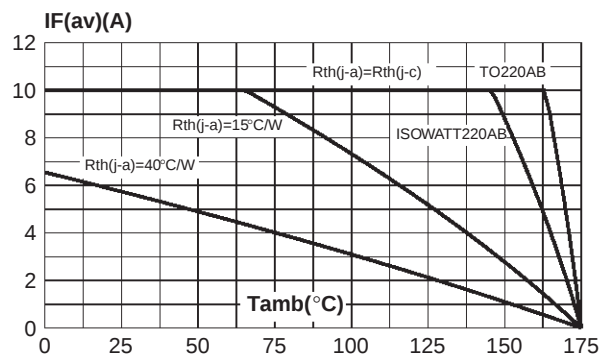


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TO-220AB, D²PAK, I²PAK)

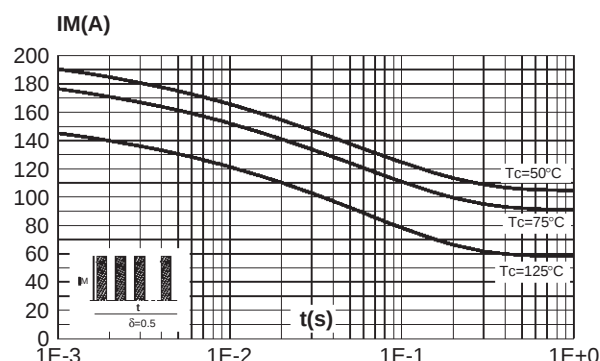


Fig. 4: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (ISOWATT220AB).

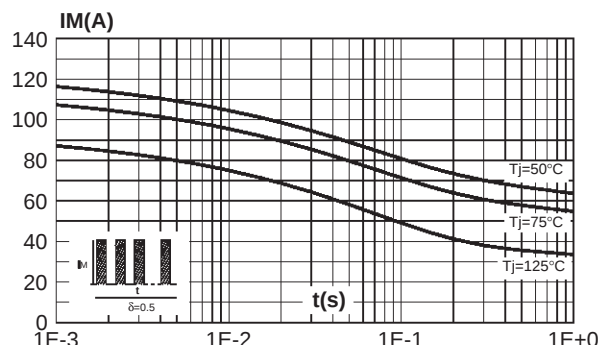


Fig. 5: Relative variation of thermal impedance junction to case versus pulse duration (per diode) (TO-220AB, D²PAK, I²PAK).

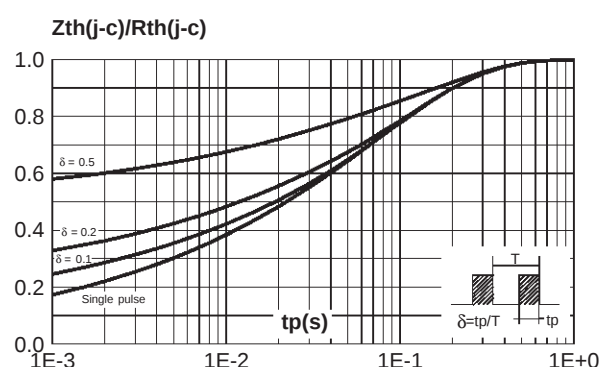


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration (per diode) (ISOWATT220AB).

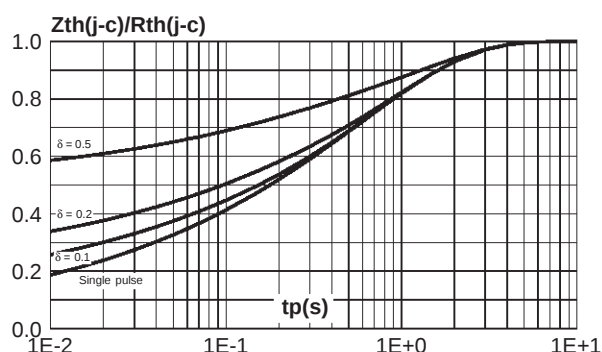


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

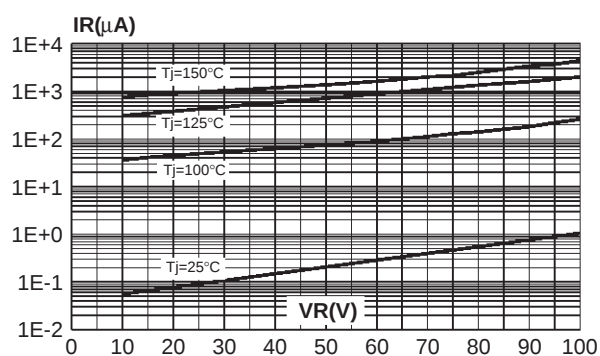
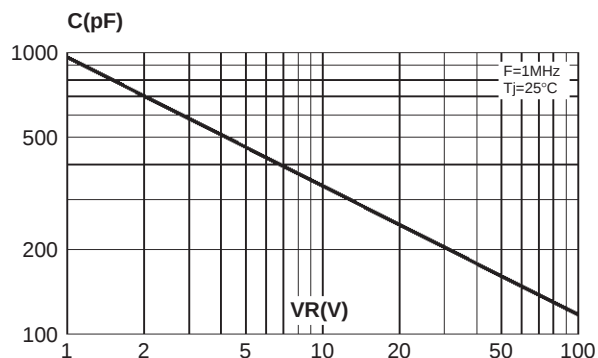


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).



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Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).

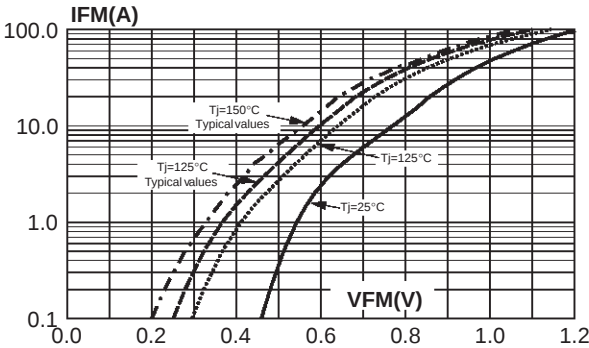
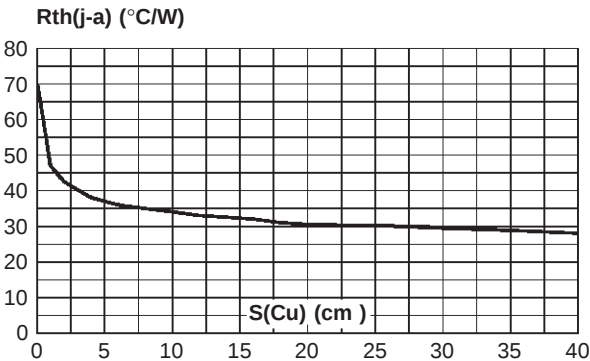
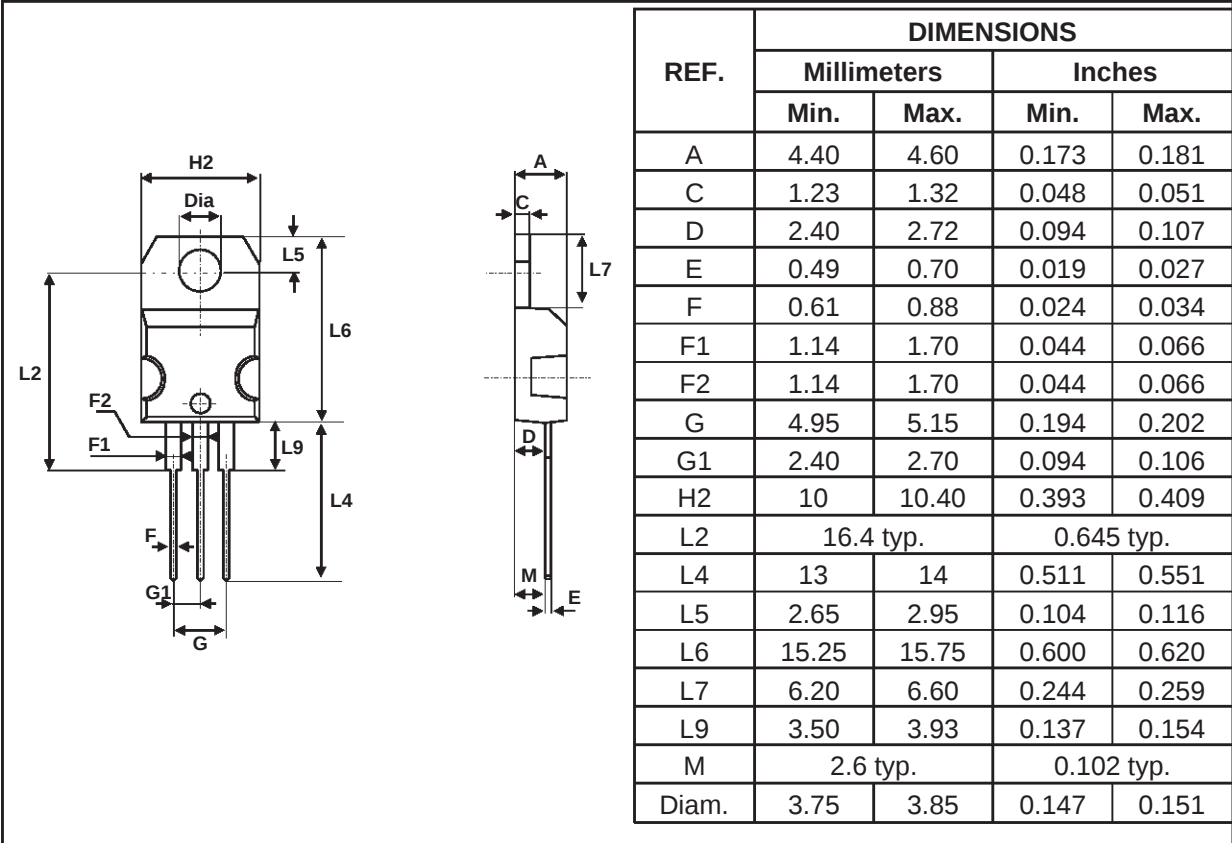
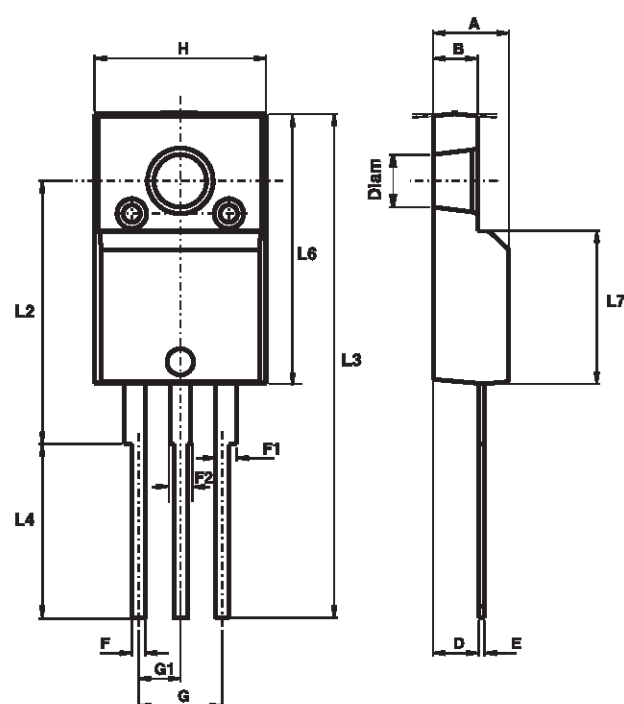


Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35μm) (D²PAK).



PACKAGE MECHANICAL DATA TO-220AB

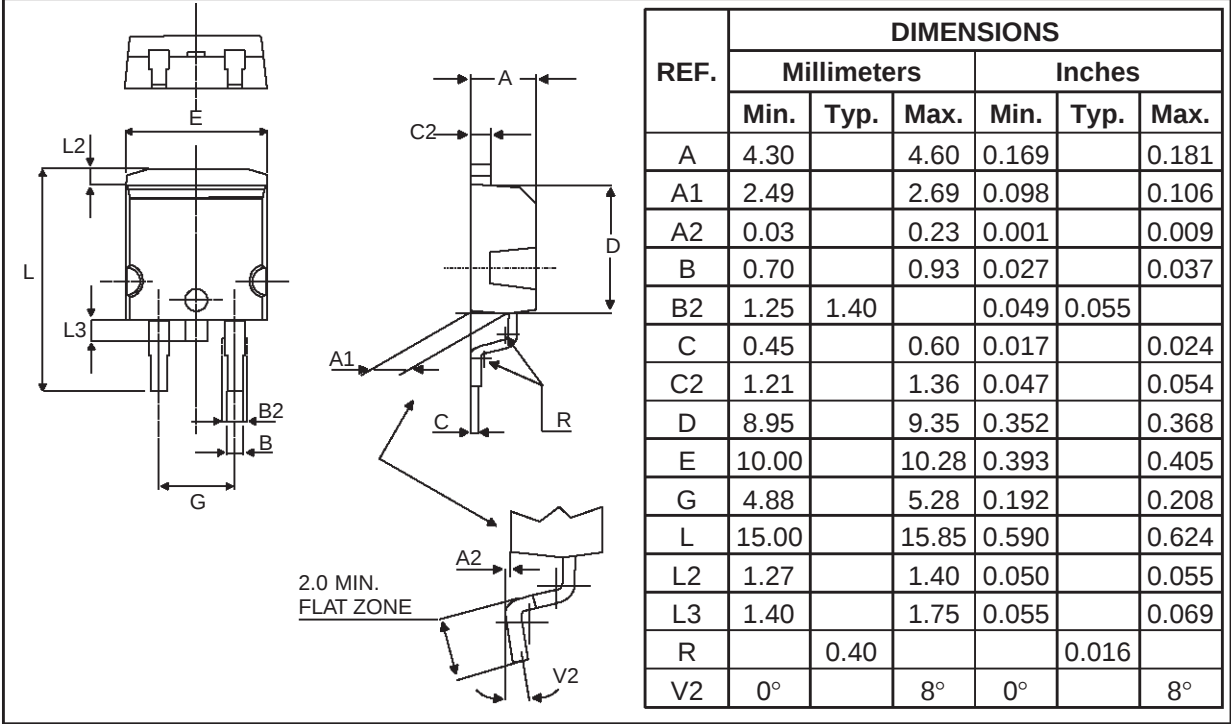


PACKAGE MECHANICAL DATA
 ISOWATT220AB


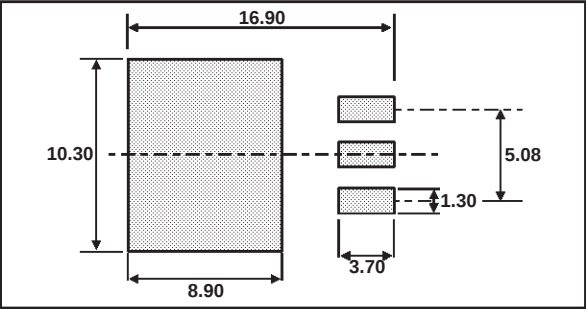
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
B	2.50	2.70	0.098	0.106
D	2.50	2.75	0.098	0.108
E	0.40	0.70	0.016	0.028
F	0.75	1.00	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.40	2.70	0.094	0.106
H	10.00	10.40	0.394	0.409
L2	16.00 typ.		0.630 typ.	
L3	28.60	30.60	1.125	1.205
L4	9.80	10.60	0.386	0.417
L6	15.90	16.40	0.626	0.646
L7	9.00	9.30	0.354	0.366
Diam	3.00	3.20	0.118	0.126

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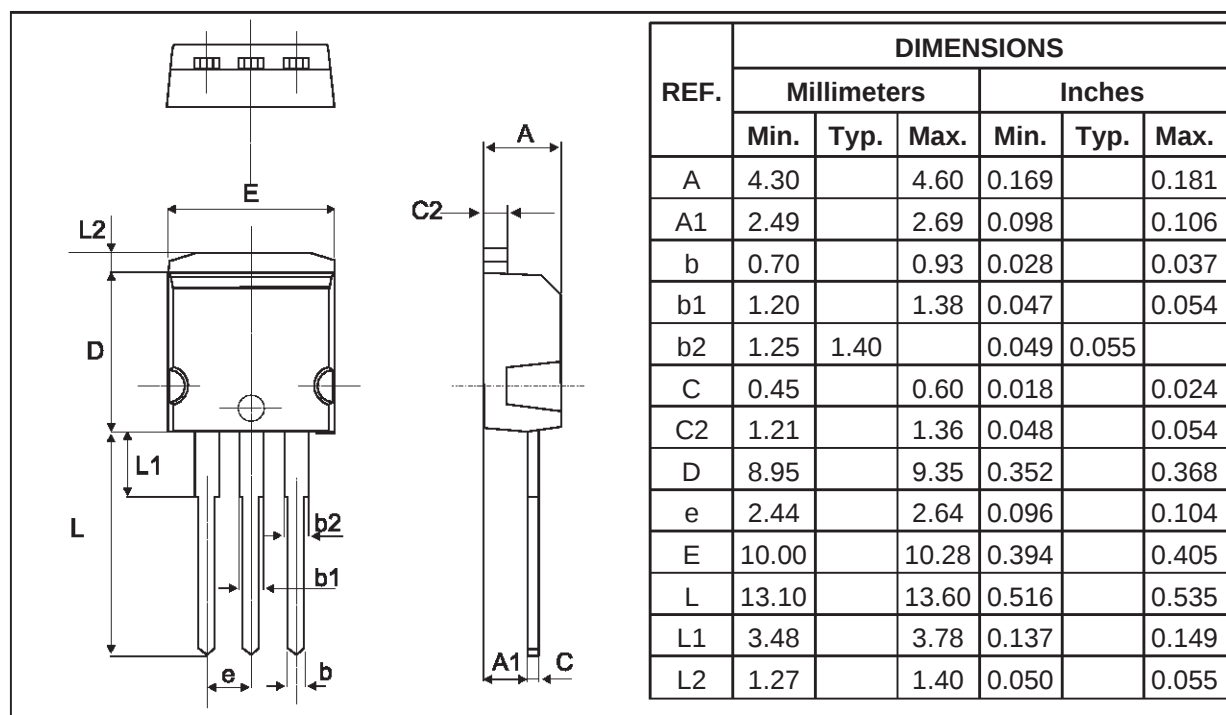
PACKAGE MECHANICAL DATA
D²PAK



FOOT PRINT DIMENSIONS (in millimeters)



PACKAGE MECHANICAL DATA

I²PAK

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20H100CT	STPS20H100CT	TO-220AB	2.20g	50	Tube
STPS20H100CF	STPS20H100CF	ISOWATT220AB	2.08g	50	Tube
STPS20H100CG-1	STPS20H100CG	I ² PAK	1.49g	50	Tube
STPS20H100CG	STPS20H100CG	D ² PAK	1.48g	50	Tube
STPS20H100CG-TR	STPS20H100CG	D ² PAK	1.48g	1000	Tape & reel

▪ Epoxy meets UL94,V0

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